



REVERSE VOLTAGE: 50 - 1000 V
CURRENT: 1.0 A

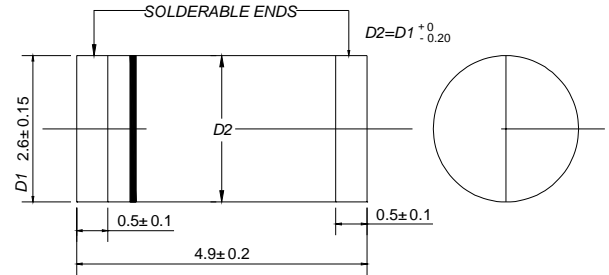
DO - 213AB

Features

- Glass passivated device
- Ideal for surface mouted applications
- Low leakage current
- Metallurgically bonded construction

Mechanical Data

- Case: JEDEC DO-213AB, molded plastic over passivated chip
- Polarity: Color band denotes cathode end
- Weight: 0.0046 ounces, 0.116 gram
- Mounting position: Any



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

		SUF 4001	SUF 4002	SUF 4003	SUF 4004	SUF 4005	SUF 4006	SUF 4007	UNITS	
Maximum recurrent peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V	
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V	
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V	
Maximum average forward rectified current $T_A=50$	$I_{(AV)}$	1.0							A	
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load (JEDEC method)	I_{FSM}	30							A	
Maximum forward voltage at 1.0A	V_F	1.0			1.7				V	
Maximum DC reverse current @ $T_j=25$ at rated DC blockjng voltage @ $T_j=100$	I_R				10		50		μA	
Maximum reverse recovery time (Note1)	t_{rr}	50			75				ns	
Typical thermal resistance (NOTE 2)	$R_{\theta JT}$				10					K/W
Typical thermal resistance (NOTE 3)	$R_{\theta JA}$				45					K/W
Operating temperature range	T_j	- 55 --- + 175								
Storage temperature range	T_{STG}	- 55 --- + 175								

NOTES:1. Measured with $I_F=0.5A$, $I_R=1A$, $I_{rr}=0.25A$.

2. Thermal resistance junction to terminal, 6.0 mm² copper pads to each terminal.

3. Thermal resistance junction to ambient, 6.0 mm² copper pads to each terminal.

Ratings AND Characteristic Curves

FIG. 1 - TYPICAL FORWARD CURRENT DERATING CURVE

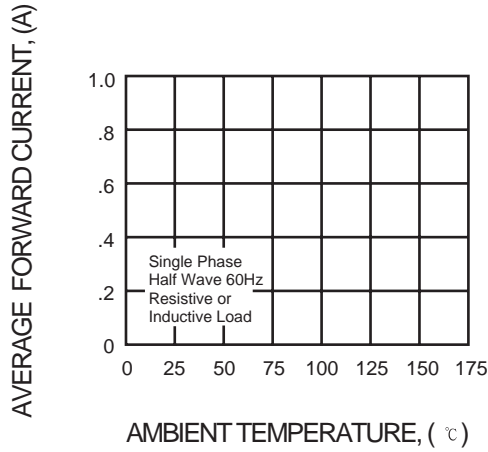


FIG. 2 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

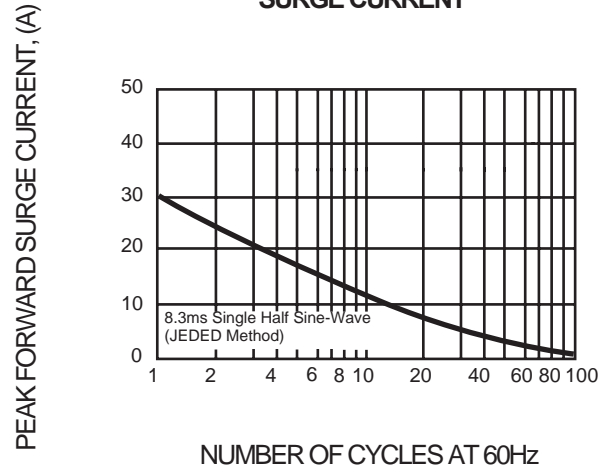


FIG. 3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

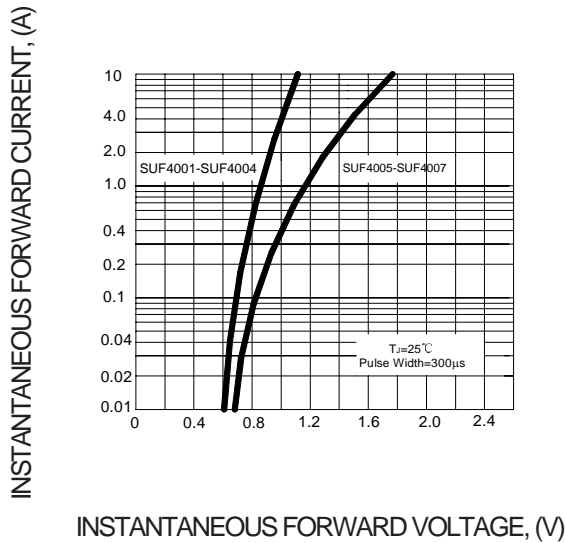


FIG. 4 - TYPICAL REVERSE CHARACTERISTICS

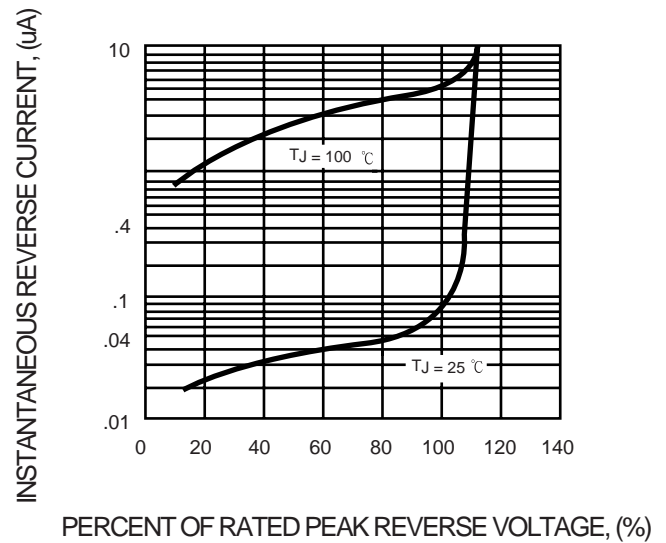
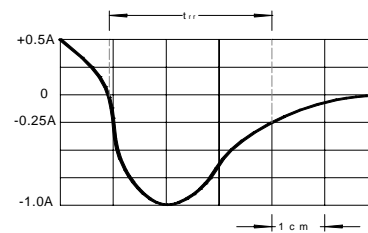
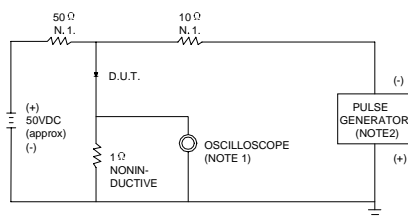


FIG.5 – TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC



NOTES:1.RISE TIME = 7ns MAX.INPUT IMPEDANCE = 1M Ω 22pF. SET TIME BASE FOR 25 ns/cm

2.RISE TIME =10ns MAX.SOURCE IMPEDANCE=50 Ω

PACKAGE	SPQ/PCS	CARTON SPQ/PCS	CARTON SIZE/CM	CARTON GW/KG	CARTON NW/KG
DO-213AB	5000/REEL	80000	36.0X35.8X36.5	18.00	16.00

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